

A2 a region on the insulating resin layer 2 in which a semiconductor device 4 is mounted to the substrate 1. On the other hand, a plurality of bump electrodes 6 are formed to the surface of the semiconductor device 4 facing the substrate 1.

✓ Page 2, first full paragraph, please delete and insert the following new paragraph:

A3 In the manufacturing method of the conventional mounting structure, at first, a plurality of the bump electrodes 6 disposed on the lower surface of the semiconductor device 4 and the mounting pad on the substrate 1 are aligned and then the semiconductor device 4 is bonded under pressure on the substrate 1. In this case, since the sealing resin 5 between the bump electrode 6 of the semiconductor device 4 and the mounting pad 3 on the substrate 1 is extruded, the bump electrode 6 and the mounting pad 3 are connected electrically with each other. In this conventional flip-chip mounting structure, since the insulating resin layer 2 having the elastic recovery force is formed between the substrate 1 and the mounting pad 3, electric connection between the bump electrode 6 and the mounting pad 3 can be held stably by the elastic recovery force of the insulating resin layer 2 and the contracting force of the sealing resin 5.

Page 4, second full paragraph, please delete and insert the following new paragraph:

A4 To achieve the above objects, the structure for mounting a semiconductor device to a substrate comprises a mounting pad disposed on the substrate, a sealing resin provided on the substrate on which the semiconductor device is to be mounted, and a plurality of projecting electrodes disposed on a surface of the semiconductor device facing the substrate, and each of the projecting electrodes including a substantially spherical portion and a pointed portion in